

Abstract of the Disclosure

A new method and structure for an improved contact using doped silicon is provided. The structures are integrated into several higher level embodiments. The improved contact has low contact resistivity. Improved junctions are thus provided
5 between an IGFET device and subsequent metallization layers. The improvements are obtained through the use of a silicon-germanium (Si-Ge) alloy. The alloy can be formed from depositing germanium onto the substrate and subsequently annealing the contact or by selectively depositing the preformed alloy into a contact opening. The above advantages are incorporated with relatively few process steps.

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